

# 2SK1611

## Silicon N-Channel Power F-MOS FET

### ■ Features

- High avalanche energy capacity
- $V_{GSS}$ : 30V guaranteed
- Low  $R_{DS(on)}$ , high-speed switching characteristic

### ■ Applications

- High-speed switching (switching power supply, AC adaptor)
- For high-frequency power amplification

### ■ Absolute Maximum Ratings ( $T_C = 25^\circ\text{C}$ )

Parameter	Symbol	Ratings	Unit
Drain to Source breakdown voltage	$V_{DSS}$	800	V
Gate to Source voltage	$V_{GSS}$	$\pm 30$	V
Drain current	DC	$I_D$	$\pm 3$ A
	Pulse	$I_{DP}$	$\pm 6$ A
Avalanche energy capacity	EAS*	20	mJ
Allowable power dissipation	$T_C = 25^\circ\text{C}$	$P_D$	50 W
	$T_a = 25^\circ\text{C}$		2 W
Channel temperature	$T_{ch}$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

\* Single pulse

### ■ Electrical Characteristics ( $T_C = 25^\circ\text{C}$ )

Parameter	Symbol	Conditions	min	typ	max	Unit	
Drain to Source cut-off current	$I_{DSS}$	$V_{DS} = 640\text{V}, V_{GS} = 0$			0.1	mA	
Gate to Source leakage current	$I_{GSS}$	$V_{GS} = \pm 30\text{V}, V_{DS} = 0$			$\pm 1$	$\mu\text{A}$	
Drain to Source breakdown voltage	$V_{DSS}$	$I_D = 1\text{mA}, V_{GS} = 0$	800			V	
Avalanche energy capacity	EAS*	$L = 4.5\text{mH}, I_D = 3\text{A}, V_{DD} = 50\text{V}$	20			mJ	
Gate threshold voltage	$V_{th}$	$V_{DS} = 25\text{V}, I_D = 1\text{mA}$	1		5	V	
Drain to Source ON-resistance	$R_{DS(on)}$	$V_{GS} = 10\text{V}, I_D = 2\text{A}$		3.2	4	$\Omega$	
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 25\text{V}, I_D = 2\text{A}$	1.5	2.4		S	
Input capacitance (Common Source)	$C_{iss}$	$V_{DS} = 20\text{V}, V_{GS} = 0, f = 1\text{MHz}$		730		pF	
Output capacitance (Common Source)	$C_{oss}$				90		pF
Reverse transfer capacitance (Common Source)	$C_{rss}$				40		pF
Turn-on time	$t_{on}$	$V_{GS} = 10\text{V}, I_D = 2\text{A}$ $V_{DD} = 200\text{V}, R_L = 100\Omega$		40		ns	
Fall time	$t_f$				35		ns
Turn-off time (delay time)	$t_{d(off)}$				105		ns

\* Avalanche energy capacity test circuit



